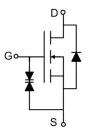


Main Product Characteristics:

V _{DSS}	30V
R _{DS} (on)	1ohm(typ.)
I _D	0.5A _☉







SOT23

Marking and pin
Assignment

Schematic diagram

Features and Benefits:

- Advanced trench MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 150°C operating temperature
- ESD Protected, HBM 1KV



Description:

It utilizes the latest trench processing techniquesto achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to makethis design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications

Absolute max Rating:

Symbol	Parameter	Max.	Units
I _D @ TC = 25°C	Continuous Drain Current, V _{GS} @ 10V	0.5 ①	
I _D @ TC = 100°C	Continuous Drain Current, V _{GS} @ 10V	0.3 ①	Α
I _{DM}	Pulsed Drain Current②	3	
P _D @TC = 25°C	Power Dissipation	0.7	W
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-to-Source Voltage	± 20	V
TJ	Operating Junction	55 to 1 150	°C
T _{STG}	Storage Temperature Range		°C

Thermal Resistance

Symbol	Characterizes	Тур.	Max.	Units
$R_{\theta JA}$	Junction-to-ambient (t ≤ 10s)③	_	180	°C/W



Electrical Characterizes $@T_A=25$ $^{\circ}$ C unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source breakdown voltage	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
R _{DS(on)}	Static Drain-to-Source on-resistance	_	1	1.5	Ω	V _{GS} =4.5V,I _D = 0.2A
R _{DS(on)}	Static Drain-to-Source on-resistance	_	2	3	Ω	V _{GS} =2.5V,I _D =0.2A
V	Cata threshold valtage	0.7	_	1.4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
$V_{GS(th)}$	Gate threshold voltage	_	0.63	_	V	T _J = 125℃
	Drain to Course leakage current	_	_	1		V _{DS} = 30V,V _{GS} = 0V
I _{DSS}	Drain-to-Source leakage current	_	_	50	μA	T _J = 125°C
	Cata to Causas famuland lanks as	_	_	10		V _{GS} =20V
I _{GSS}	Gate-to-Source forward leakage	_	_	-10	μA	V _{GS} = -20V
Qg	Total gate charge	_	1.15	_		I _D = 0.1A,
Q _{gs}	Gate-to-Source charge	_	0.35	_	nC	V _{DS} =20V,
Q_{gd}	Gate-to-Drain("Miller") charge	_	0.25	_		V _{GS} = 4.5V
t _{d(on)}	Turn-on delay time	_	15	_		
tr	Rise time	_	45	_		V _{GS} =4.5V, V _{DS} =5V,
t _{d(off)}	Turn-Off delay time	_	65	_	ns	$R_{GEN}=50\Omega$, $I_{D}=0.1A$,
t _f	Fall time	_	65	_		
C _{iss}	Input capacitance	_	20	_		V _{GS} = 0V,
Coss	Output capacitance	_	18	_	pF	V _{DS} =15V,
C _{rss}	Reverse transfercapacitance	_	7	_		f = 1MHz

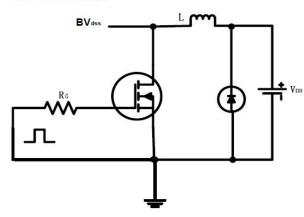
Source-Drain Ratings and Characteristics

Symbol	Parameter	Min.	Тур.	Max.	Units	Conditions
I.	Continuous Source Current		_	0.5 ①	Α	MOSFET symbol
Is	(Body Diode)					showing the
I _{SM}	Pulsed Source Current	_	_	3	Α	integral reverse
	(Body Diode)					p-n junction diode.
V _{SD}	Diode Forward Voltage	_	0.72	1.2	V	I _S =0.3A, V _{GS} =0V

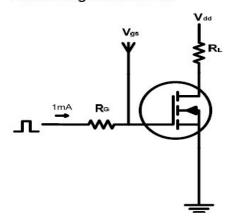


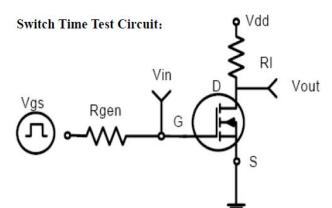
Test circuits and Waveforms

EAS test circuits:

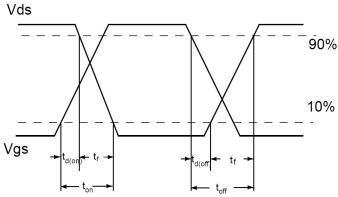


Gate charge test circuit:





Switch Waveforms:

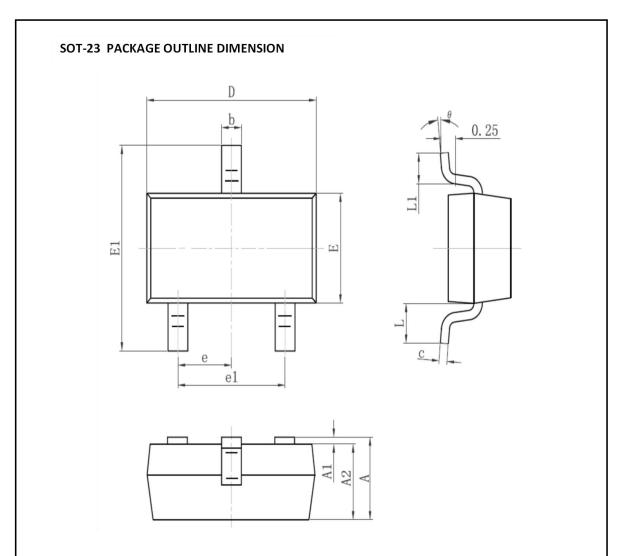


Notes:

- ①Calculated continuous current based on maximum allowablejunction temperature.
- ②Repetitive rating; pulse width limited by max junction temperature.
- 4 These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming amaximum junction temperature of $T_{J(MAX)}=150$ °C.



Mechanical Data:



Symbol	Dimension I	Dimension In Millimeters		n In Inches
Symbol	Min	Max	Min	Max
Α	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
С	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.95	TYP	0.03	7TYP
e1	1.800	2.000	0.071	0.079
L	0.55REF		0.02	2REF
L1	0.300	0.500	0.012	0.020
θ	00	8 ⁰	00	8 ⁰



Ordering and Marking Information

Device Marking: 3002

Package (Available)
SOT-23
Operating Temperature Range
C: -55 to 150 °C

Devices per Unit

Package	Units/	Tubes/Inner	Units/Inner	Inner	Units/Carton
Type	Tube	Box	Box	Boxes/Carton	Box
				Box	
SOT23	3000	10	30000	4	120000

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High	Tj= 150℃ @ 80% of	168 hours	3 lots x 77 devices
Temperature	Max V _{DSS} /V _{CES} /V _R	500 hours	
Reverse		1000 hours	
Bias(HTRB)			
High	Tj=150℃ @ 100% of	168 hours	3 lots x 77 devices
Temperature	Max V _{GSS}	500 hours	
Gate		1000 hours	
Bias(HTGB)			



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